**Product data sheet** 

## 1. General description

P-channel enhancement mode Field-Effect Transistor (FET) in a small SOT23 (TO-236AB) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

### 2. Features and benefits

- · Low threshold voltage
- Trench MOSFET technology
- · Very fast switching
- AEC-Q101 qualified

## 3. Applications

- Relay driver
- · High-speed line driver
- · High-side load switch
- · Switching circuits

### 4. Quick reference data

#### Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
$V_{DS}$	drain-source voltage	T <sub>j</sub> = 25 °C		-	-	-28	V
$V_{GS}$	gate-source voltage			-12	-	12	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = -4.5 V; T <sub>amb</sub> = 25 °C	[1]	-	-	-4	Α
Static char	racteristics						
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS}$ = -4.5 V; $I_D$ = -4 A; $T_j$ = 25 °C		-	41	50	mΩ

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for drain 6 cm<sup>2</sup>.



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# 5. Pinning information

#### **Table 2. Pinning information**

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	3	D
2	S	source		
3	D	drain		G (F)
			1 2	s
			SOT23	017aaa094

# 6. Ordering information

#### **Table 3. Ordering information**

Type number	Package				
	Name	Description	Version		
PMV41XPA		plastic, surface-mounted package; 3 terminals; 1.9 mm pitch; 2.9 mm x 1.3 mm x 1 mm body	SOT23		

# 7. Marking

#### Table 4. Marking codes

Type number	Marking code[1]
PMV41XPA	%5н

[1] % = placeholder for manufacturing site code

## 8. Limiting values

#### **Table 5. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> = 25 °C		-	-28	V
V <sub>GS</sub>	gate-source voltage			-12	12	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = -4.5 V; T <sub>amb</sub> = 25 °C	[1]	-	-4	Α
		V <sub>GS</sub> = -4.5 V; T <sub>amb</sub> = 100 °C	[1]	-	-3	Α
I <sub>DM</sub>	peak drain current	T <sub>amb</sub> = 25 °C; single pulse; t <sub>p</sub> ≤ 10 μs		-	-38	Α
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> = 25 °C	[2]	-	510	mW
			[1]	-	1.2	W
		T <sub>sp</sub> = 25 °C		-	7	W
Tj	junction temperature			-55	150	°C
T <sub>amb</sub>	ambient temperature			-55	150	°C
T <sub>stg</sub>	storage temperature			-65	150	°C
Source-drain	n diode					
Is	source current	T <sub>amb</sub> = 25 °C	[1]	-	-1.2	Α
Avalanche r	uggedness	,	1	1	-	
E <sub>DS(AL)S</sub>	non-repetitive drain- source avalanche energy	T <sub>j(init)</sub> = 25 °C; I <sub>D</sub> = -1.1 A; DUT in avalanche (unclamped)		-	17.5	mJ

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for drain 6 cm<sup>2</sup>.
- [2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

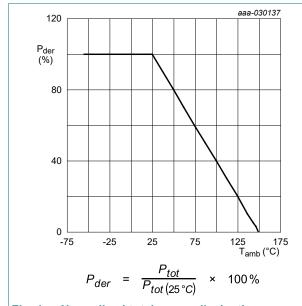


Fig. 1. Normalized total power dissipation as a function of ambient temperature

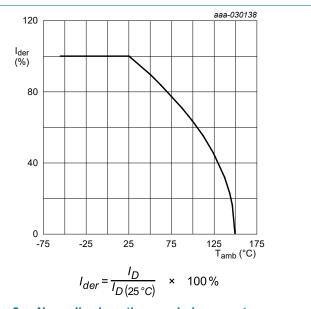


Fig. 2. Normalized continuous drain current as a function of ambient temperature

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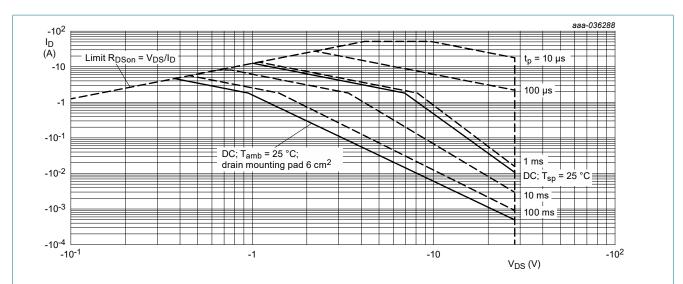


Fig. 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-source voltage

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## 9. Thermal characteristics

**Table 6. Thermal characteristics** 

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R <sub>th(j-a)</sub>	thermal resistance from	in free air	[1]	-	208	245	K/W
	junction to ambient		[2]	-	88	104	K/W
$R_{th(j-sp)}$	thermal resistance from junction to solder point			-	13	18	K/W

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for drain 6 cm<sup>2</sup>.

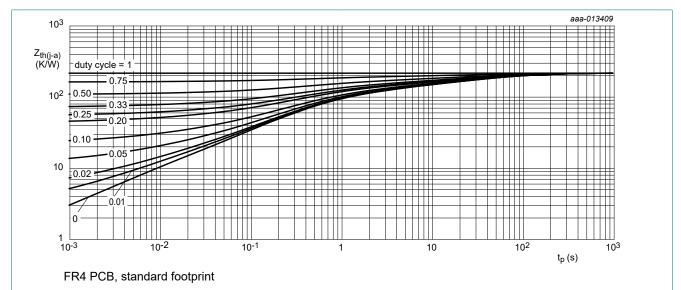


Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

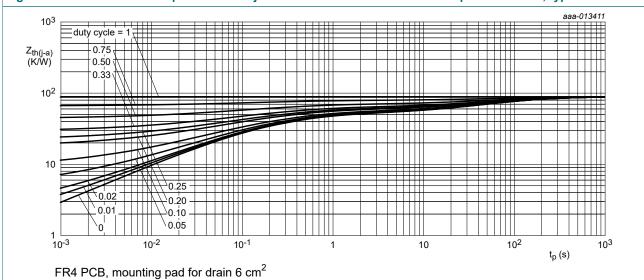


Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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## 10. Characteristics

### **Table 7. Characteristics**

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics					
V <sub>(BR)DSS</sub>	drain-source breakdown voltage	$I_D$ = -250 $\mu$ A; $V_{GS}$ = 0 V; $T_j$ = 25 °C	-28	-	-	V
$V_{GSth}$	gate-source threshold voltage	$I_D$ = -250 $\mu$ A; $V_{DS}$ = $V_{GS}$ ; $T_j$ = 25 °C	-0.45	-0.68	-1	V
I <sub>DSS</sub>	drain leakage current	V <sub>DS</sub> = -28 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	-1	μΑ
I <sub>GSS</sub>	gate leakage current	V <sub>GS</sub> = -12 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	-100	nA
		V <sub>GS</sub> = 12 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	100	nA
R <sub>DSon</sub>	drain-source on-state	$V_{GS} = -4.5 \text{ V}; I_D = -4 \text{ A}; T_j = 25 ^{\circ}\text{C}$	-	41	50	mΩ
	resistance	V <sub>GS</sub> = -4.5 V; I <sub>D</sub> = -4 A; T <sub>j</sub> = 150 °C	-	63	80	mΩ
		$V_{GS}$ = -2.5 V; $I_D$ = -2.5 A; $T_j$ = 25 °C	-	49	64	mΩ
		$V_{GS}$ = -1.8 V; $I_D$ = -0.5 A; $T_j$ = 25 °C	-	67	105	mΩ
9 <sub>fs</sub>	forward transconductance	$V_{DS} = -10 \text{ V}; I_D = -4 \text{ A}; T_j = 25 \text{ °C}$	-	12	-	S
$R_G$	gate resistance	f = 1 MHz	-	5.2	-	Ω
Dynamic ch	aracteristics					
Q <sub>G(tot)</sub>	total gate charge	V <sub>DS</sub> = -15 V; I <sub>D</sub> = -4 A; V <sub>GS</sub> = -4.5 V;	-	14	21	nC
Q <sub>GS</sub>	gate-source charge	T <sub>j</sub> = 25 °C	-	1.9	-	nC
$Q_{GD}$	gate-drain charge		-	3.7	-	nC
C <sub>iss</sub>	input capacitance	V <sub>DS</sub> = -15 V; f = 1 MHz; V <sub>GS</sub> = 0 V;	-	1254	-	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C	-	88	-	pF
C <sub>rss</sub>	reverse transfer capacitance		-	77	-	pF
t <sub>d(on)</sub>	turn-on delay time	V <sub>DS</sub> = -15 V; I <sub>D</sub> = -4 A; V <sub>GS</sub> = -4.5 V;	-	4	-	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 6 \Omega; T_j = 25 °C$	-	10	-	ns
t <sub>d(off)</sub>	turn-off delay time		-	42	-	ns
t <sub>f</sub>	fall time	]	-	18	-	ns
Source-drai	in diode					
V <sub>SD</sub>	source-drain voltage	I <sub>S</sub> = -1.9 A; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-0.74	-1.2	V
t <sub>rr</sub>	reverse recovery time	$I_S = -1.9 \text{ A}; \text{ d}I_S/\text{d}t = 100 \text{ A/}\mu\text{s};$	-	11.6	-	ns
Q <sub>r</sub>	recovered charge	$V_{GS} = -4.5 \text{ V}; V_{DS} = -15 \text{ V}; T_j = 25 \text{ °C}$	-	3.8	-	nC

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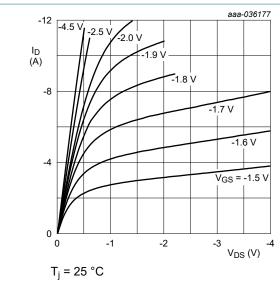


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values

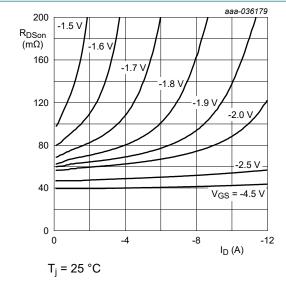


Fig. 8. Drain-source on-state resistance as a function of drain current; typical values

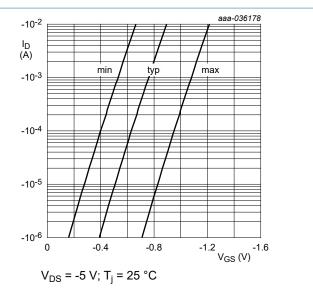


Fig. 7. Sub-threshold drain current as a function of gate-source voltage

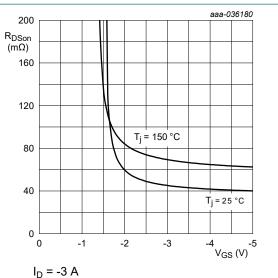


Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

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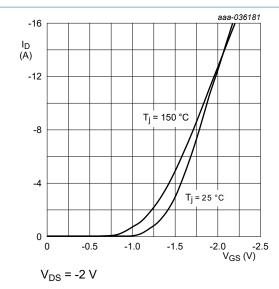


Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

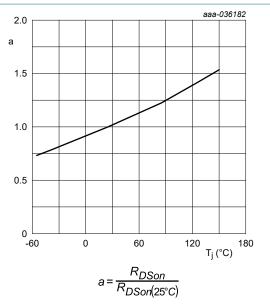


Fig. 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values

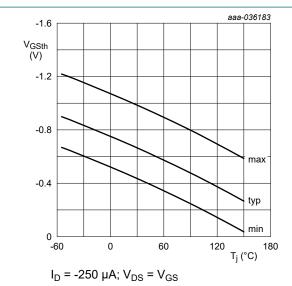
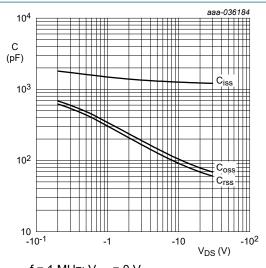


Fig. 12. Gate-source threshold voltage as a function of junction temperature



 $f = 1 MHz; V_{GS} = 0 V$ 

Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

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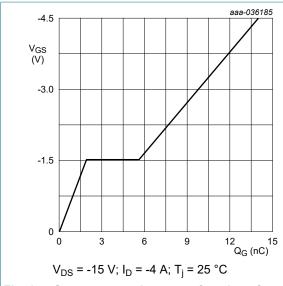


Fig. 14. Gate-source voltage as a function of gate charge; typical values

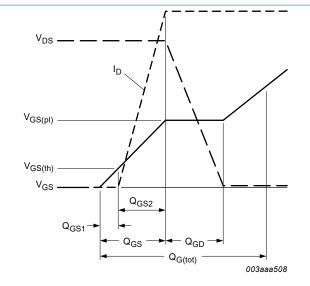


Fig. 15. Gate charge waveform definitions

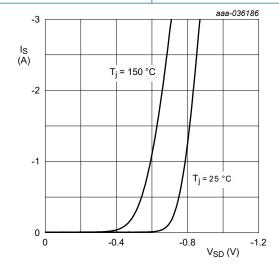
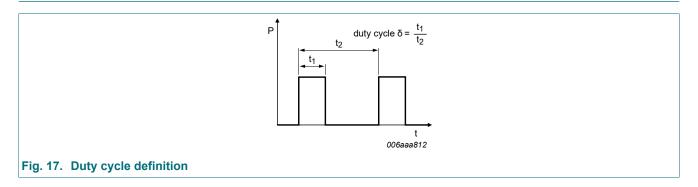


Fig. 16. Source current as a function of source-drain voltage; typical values

 $V_{GS} = 0 V$ 

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## 11. Test information

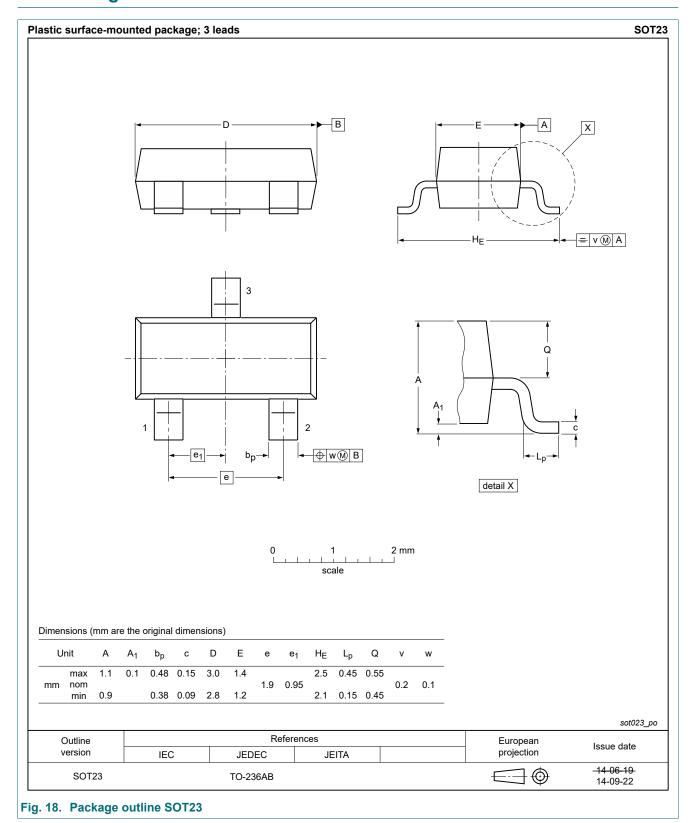


### **Quality information**

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

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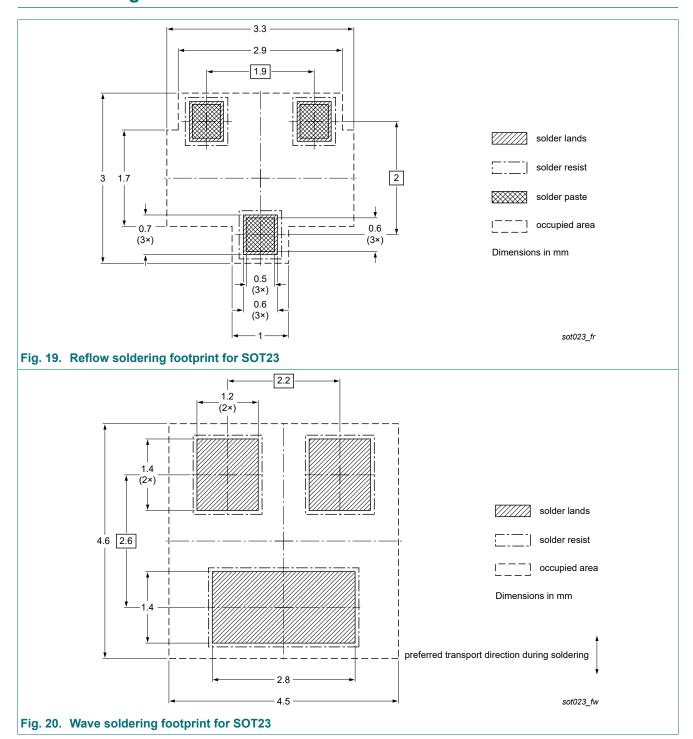
## 12. Package outline



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## 13. Soldering



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# 14. Revision history

#### **Table 8. Revision history**

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes				
PMV41XPA v.2	20230712	Product data sheet	-	PMV41XPA v.1				
Modifications:	Change I <sub>D</sub> condition	Change I <sub>D</sub> condition for one R <sub>DSon</sub> parameter						
PMV41XPA v.1	20230306	Product data sheet	-	-				

#### 28 V, P-channel Trench MOSFET

## 15. Legal information

#### **Data sheet status**

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
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